

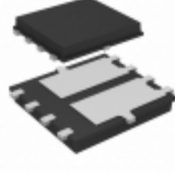
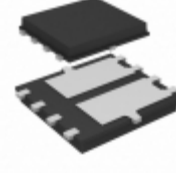
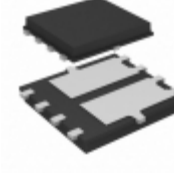
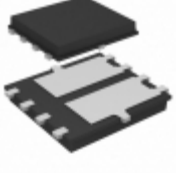
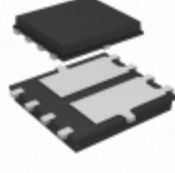
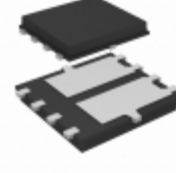
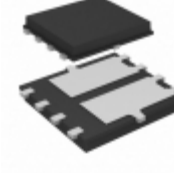
	<h2>SI7911DN-T1-E3</h2>
	<p><b>Hersteller-Teilenummer:</b> SI7911DN-T1-E3</p> <p><b>Hersteller / Marke:</b> Electro-Films (EFI) / Vishay</p> <p><b>Teil der Beschreibung:</b> MOSFET 2P-CH 20V 4.2A 1212-8</p> <p><b>Datenblätter:</b>  <a href="#">SI7911DN-T1-E3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 108053 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	SI7911DN-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET 2P-CH 20V 4.2A 1212-8
Kategorie	<a href="#">Diskrete Halbleiterprodukte</a> > <a href="#">Transistoren-FETs</a> ,
Teilstatus	108053 pcs Stock
detaillierte Beschreibung	Mosfet Array 2 P-Channel (Dual) 20V 4.2A 1.3W
Serie	TrenchFET®
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Leistung - max	1.3W
Verpackung / Gehäuse	PowerPAK® 1212-8 Dual
Supplier Device-Gehäuse	PowerPAK® 1212-8 Dual
Typ FET	2 P-Channel (Dual)
FET-Merkmal	Logic Level Gate
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.2A
Rds On (Max) @ Id, Vgs	51 mOhm @ 5.7A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	15nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Cut Tape (CT)
Basisteilenummer	SI7911
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI7911DN-T1-E3CT

SI7911DN-T1-E3 ist neu im Original, Suche SI7911DN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7911DN-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI7911DN-T1-E3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI7911DN</b> VISHAY SI7911DN VISHAY</p>	 <p><b>SI7911DN-T1-E3</b> Vishay / Siliconix MOSFET 2P-CH 20V 4.2A 1212-8</p>	 <p><b>SI7911DN-T1-GE3</b> Vishay / Siliconix MOSFET 2P-CH 20V 4.2A 1212-8</p>	 <p><b>SI7911DN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET 2P-CH 20V 4.2A 1212-8</p>
 <p><b>SI7909DN-T1-GE3</b> Vishay / Siliconix MOSFET 2P-CH 12V 5.3A 1212-8</p>	 <p><b>SI7909DN-T1-E3</b> Vishay / Siliconix MOSFET 2P-CH 12V 5.3A 1212-8</p>	 <p><b>SI7909DN-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET 2P-CH 12V 5.3A 1212-8</p>	 <p><b>SI7913DN-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET 2P-CH 20V 5A 1212-8</p>

### heiße Teile

Mehr

SI7900EDN	SI7900EDN-T1	SI7900EDN-T1-E3	SI7900EDN-T1-GE3	SI7901EDN-T1
SI7901EDN-T1-E3	SI7901EDN-T1-E3	SI7904BDN-T1-E3	SI7904BDN-T1-E3	SI7904BDN-T1-GE3
SI7904BDN-T1-GE3	SI7904DN	SI7904DN-T1	SI7904DN-T1-E3	SI7904DN-T1-E3
SI7904DN-T1-GE3	SI7904DN-T1-GE3	SI7905DN-T1-GE3	SI7905DN-T1-GE3	SI7909DN-T1-E3
SI7909DN-T1-E3	SI7909DN-T1-GE3	SI7909DN-T1-GE3	SI7911DN	SI7911DN-T1-E3
SI7911DN-T1-GE3	SI7911DN-T1-GE3	SI7913DN-T1-E3	SI7913DN-T1-E3	SI7913DN-T1-GE3
SI7913DN-T1-GE3	SI7922DN-T1-E3	SI7922DN-T1-E3	SI7922DN-T1-GE3	SI7922DN-T1-GE3
SI7923DN-T1-E3	SI7923DN-T1-E3	SI7923DN-T1-GE3	SI7923DN-T1-GE3	SI7938DP-T1-GE3
SI7938DP-T1-GE3	SI7940DP	SI7940DP-T1-E3	SI7940DP-T1-E3	SI7941DP-T1-E3
SI7941DP-T1-GE3	SI7942DP	SI7942DP-T1-E3	SI7942DP-T1-E3	SI7942DP-T1-GE3

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